L Number	Hits	Search Text	DB	Time stamp
3	1480	(257/316).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:52
6	474	(257/303).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:52
7	155	(257/929).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:53
8	51	(438/222).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:57
9	876	(257/368).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:54
10	42	(257/41).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:54
11	34	(257/44).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:56
12	751	(257/288).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:57
13	732	(257/592).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:57
14	242	(438/350).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:57
-	10	(("5393681") or ("6391692") or ("5308782") or ("5998248") or ("6319782")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 06:43
-	162	257/929 and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 14:45
-	542	438/300 and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 14:44
-	4	@ad<=20010323 and 'raised vertical lateral transistor'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 16:02

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-	1	@ad<=20010323 and 'raised source and drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:26
-	1	@ad<=20010323 and 'epitaxial' and 'source or drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:30
-	8	@ad<=20010323 and 'epitaxial' and 'source and drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:30
-	3470	gardner.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:45
-	6	gardner.inv. and 'vertical transistor' and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 15:48
-	4	@ad<=20010323 and 'elevated source and drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:24
-	257	@ad<=20010323 and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 16:06
-	37	@ad<=20010323 and 'epitaxial' with 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 14:23
-	1	"4728623".PN.	USPAT	2002/09/04 16:31
-	1	"4738937".PN.	USPAT	2002/09/04 16:31
-	1	"4918029".PN.	USPAT	2002/09/04 16:31
-	1	"5004702".PN.	USPAT	2002/09/04 16:31
-	1	"5030583".PN.	USPAT	2002/09/04 16:31
-	1	"5032538".PN.	USPAT	2002/09/04 16:31
-	1	"5045494".PN.	USPAT	2002/09/04 16:31
-	1	"5272109".PN.	USPAT	2002/09/04 16:32
-	1	"5496750".PN.	USPAT	2002/09/04 16:38
-	1	"5378651".PN.	USPAT	2002/09/04 16:38
-	1	"5321306".PN.	USPAT	2002/09/04 16:38
-	1	"5296388".PN.	USPAT	2002/09/04 16:38
-	1	"5250454".PN.	USPAT	2002/09/04 16:39
-	1	"5213991".PN.	USPAT	2002/09/04 16:39
-	1	"5079180".PN.	USPAT	2002/09/04 16:39
-	1	"5057899".PN.	USPAT	2002/09/04 16:39

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–	1	"4966861".PN.	USPAT	2002/09/04 16:41
–	1	"4814841".PN.	USPAT	2002/09/04 16:48
–	1	"5057893".PN.	USPAT	2002/09/04 16:48
–	18	(("6096596") or ("6090691") or ("6057200") or ("6001697") or ("5998844") or ("5963822") or ("5945698") or ("5933738") or ("5863826")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 08:23
–	18	(("5831334") or ("5677573") or ("5641694") or ("5600161") or ("5497017") or ("5312768") or ("5156987") or ("5122476") or ("5087586")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 10:18
–	2	("5308782").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 10:19
–	2	("6319782").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/05 10:19
–	1731	((438/300) or (257/302) or (257/929) or (257/592)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 08:44
–	12	ri-seiko.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 08:44
–	38	@ad<=20010323 and 'epitaxial' with 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:33
–	263	@ad<=20010323 and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:33
–	263	@ad<=20010323 and elevated adj1 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:02
–	95	@ad<=20010323 and elevated adj1 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:02
–	112	@ad<=20010323 and raised adj1 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:03
–	229	@ad<=20010323 and raised adj1 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:03
–	0	@ad<=20010323 and 'epitaxial silicon gate' with 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:38

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-	20	@ad<=20010323 and 'silicon gate' and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 09:38
-	47	@ad<=20010323 and 'polysilicon gate' and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:14
-	0	@ad<=20010323 and 'epitaxial polysilicon gate' and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:25
-	1	@ad<=20010323 and 'epitaxial polysilicon' and 'elevated source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 10:08
-	56	@ad<=20010323 and 'epitaxial polysilicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:20
-	0	@ad<=20010323 and 'epitaxial polysilicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 14:05
-	24	@ad<=20010323 and 'epitaxial gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 14:05
-	24	@ad<=20010323 and 'epitaxial gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:30
-	560	@ad<=20010323 and polysilicon with epitaxial with gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:16
-	2348	@ad<=20010323 and 'multilayer' same 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:55
-	260	(@ad<=20010323 and 'multilayer' same 'gate') and 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/20 16:18
-	0	@ad<=20010323 and 'multilayer gate' with 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:33
-	1	@ad<=20010323 and epitaxial near grow near polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:20
-	693	@ad<=20010323 and 'epitaxial silicon' same 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:32

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-	367	@ad<=20010323 and 'epitaxial silicon' with 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:41
-	9	@ad<=20010323 and 'epitaxial silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 10:14
-	1	@ad<=20010323 and 'multilayer silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 08:56
-	1	("6534809").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 13:55
-	564	@ad<=20010323 and 'polysilicon gate' same 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:18
-	390	(257/756).ccls and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 14:43
-	214	@ad<=20010323 and 'floating gate' same 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:18
-	2141	@ad<=20010323 and 'elevated' same 'source' and 'drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:28
-	413	@ad<=20010323 and 'elevated' with 'source' with 'drain'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 14:28
-	6	@ad<=20010323 and 'epi silicon' and 'elevated' same 'source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 06:45
-	1	"4074300".PN.	USPAT	2003/03/25 14:37
-	32	@ad<=20010323 and 'gate stack' and 'elevated' same 'source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 15:13
-	8	(("4583105") or ("6083815") or ("5885877") or ("5986328")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 15:39
-	2	("5198378").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 15:39
-	92	@ad<=20010323 and 'epi' and 'silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 11:54

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-	9	@ad<=20010323 and 'epitaxial silicon gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 11:10
-	1	("6528363").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 11:10
-	7	@ad<=20010323 and 'conductor' same 'epi' same 'polysilicon' same 'amorphous'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:31
-	0	@ad<=20010323 and 'conductive' same 'epi' same 'polysilicon' same 'amorphous'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 12:04
-	3	("6335251").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:34
-	2	("6232641").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:01
-	2	("6171910").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:20
-	2	("6051473").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 15:20
-	8	@ad<=20010323 and 'epi silicon' and 'raised' same 'source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 14:42
-	9	@ad<=20010323 and 'epitaxial' adj1 'silicon' adj1 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 14:36
-	24	@ad<=20010323 and 'epitaxial' adj1 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 14:36
-	11	@ad<=20010323 and 'epi silicon' and 'raised' same 'source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/24 14:42
-	394	(257/756).ccls and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:50
-	600	438/300 and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:58

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-	2	("6534809").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 06:43
-	173	@ad<=20010323 and 'epitaxial' adj1 'silicon' and 'elevated' same 'source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 13:32
-	2	@ad<=20010323 and 'epitaxial' adj1 'silicon gate' and 'elevated' same 'source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 06:46
-	43	@ad<=20010323 and 'gate' with 'epitaxial' adj1 'silicon' and 'elevated' same 'source'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 07:35
-	17	@ad<=20010323 and 'transistor gate' with 'epitaxial' adj1 'silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 07:45
-	143	@ad<=20010323 and 'transistor gate' with 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 09:33
-	238	@ad<=20010323 and 'epitaxial' adj2 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:08
-	2	@ad<=20010323 and 'stacked gate' with 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:33
-	243	(438/657).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 16:48
-	225	(438/647).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:56
-	118	(257/385).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:56
-	534	(257/382).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:59
-	225	(438/647).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:57
-	313	(438/300).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:58

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-	69	(257/381).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:59
-	244	(257/756).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 08:59
-	197	@ad<=20010323 and 'polysilicon gate' with 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/25 09:36
-	0	@ad<=20010323 and 'epitaxial silicon' with 'selected silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 11:35
-	238	@ad<=20010323 and 'single' with 'poly' with 'amorphous'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 14:09
-	386	@ad<=20010323 and 'epitaxial silicon' with 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 11:42
-	88	@ad<=20010323 and 'gate electrode' with 'epitaxial silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 13:07
-	5	@ad<=20010323 and 'epitaxial' near 'gate' near 'silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 13:11
-	68	@ad<=20010323 and 'epitaxial' near 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 13:19
-	14	@ad<=20010323 and 'epitaxial silicon' near 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 13:19
-	187	@ad<=20010323 and 'epitaxial silicon' near4 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 13:47
-	138	@ad<=20010323 and 'epitaxial silicon' near3 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 13:20
-	2	("6534809").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 13:47
-	428	@ad<=20010323 and 'schottky gate' and 'epitaxial'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 14:12

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-	8	@ad<=20010323 and 'schottky gate' and 'epitaxial silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 14:18
-	1971	@ad<=20010323 and 'epitaxial silicon' near1 'layers'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 14:34
-	13	@ad<=20010323 and 'epitaxial silicon' near1 'layers' near1 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 14:34
-	65	@ad<=20010323 and 'epitaxial silicon' near1 'layers' near2 'gate'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:11
-	2	("5110748").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:37
-	1	"3959045".PN.	USPAT	2003/11/12 15:12
-	1	"3997381".PN.	USPAT	2003/11/12 15:12
-	1	"4292730".PN.	USPAT	2003/11/12 15:13
-	1	"4888304".PN.	USPAT	2003/11/12 15:13
-	1	"4891329".PN.	USPAT	2003/11/12 15:14
-	1	"4983251".PN.	USPAT	2003/11/12 15:14
-	1	"5006487".PN.	USPAT	2003/11/12 15:15
-	1	"5006487".PN.	USPAT	2003/11/12 15:16
-	1	"5013681".PN.	USPAT	2003/11/12 15:17
-	0	("candelaria.in.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:38
-	0	("candelaria-jon.in.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:37
-	0	("candelaria-jon-j.in.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:38
-	0	("Candelaria-jon-j.in.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:39
-	65	candelaria.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:38

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-	6	Candelaria-jon-j.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/12 15:39
-	2	"20020137269"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 09:22
-	2	"20020093054"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:09
-	2	"20010019137"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:11
-	2	("6630721").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:13
-	2	("6433382").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:26
-	1	"5739567".PN.	USPAT	2004/03/18 10:19
-	1	"5627395".PN.	USPAT	2004/03/18 10:34
-	2	("6150688").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:33
-	2	("6037202").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:34
-	22	((("5994735") or ("5886382") or ("5780327") or ("5612563") or ("5612230") or ("5595920") or ("5578850") or ("5574299") or ("4447889") or ("5483094") or ("5460994")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 10:49
-	108	@ad<=20010323 and 'vertical' with 'transistor' same 'epitaxial silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 13:34
-	47	@ad<=20010323 and 'vertical' with 'transistor' with 'epitaxial silicon'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/18 13:34

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